

# NOT RECOMMENDED FOR NEW DESIGN USE DMN2024U



DMG6968U

#### N-CHANNEL ENHANCEMENT MODE MOSFET

#### **Features**

- Low On-Resistance
  - $25m\Omega$  @  $V_{GS} = 4.5V$
  - 29mΩ @ V<sub>GS</sub> = 2.5V
  - 36mΩ @ V<sub>GS</sub> = 1.8V
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Up To 2kV
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part.
   A listing can be found at

https://www.diodes.com/products/automotive/automotive-products/.

 This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.

https://www.diodes.com/quality/product-definitions/

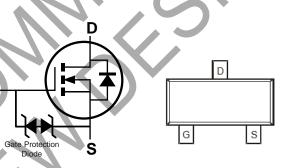
 An Automotive-Compliant Part is Available Under Separate Datasheet (<u>DMG6968UQ</u>)





### **Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.
  UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
  Solderable per MIL-STD-202, Method 208 3
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (Approximate)



Top View

#### Ordering Information (Note 4)

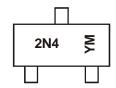
**ESD PROTECTED TO 2kV** 

Part Number	Compliance	Case	Packaging
DMG6968U-7	Standard	SOT23	3000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

### **Marking Information**



2N4 = Product Type Marking Code YM = Date Code Marking Y or  $\overline{Y}$  = Year (ex: G = 2019) M = Month (ex: 9 = September)

Date Code Key

Year	2009		2019	2020	2021	2022	2023	2024	2025	2026	2027	2028
Code	W		G	Н	1	J	K	L	М	N	0	Р
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



## **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characte	eristic		Symbol	Value	Unit
Drain-Source Voltage		VDSS	20	V	
Gate-Source Voltage		V <sub>GSS</sub>	±12	V	
Continuous Drain Current (Note 5)	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	6.5 5.2	Α	
Pulsed Drain Current		IDM	30	А	

### **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	PD	1.3	W
Thermal Resistance, Junction to Ambient @ T <sub>A</sub> = +25°C	Reja	157	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C

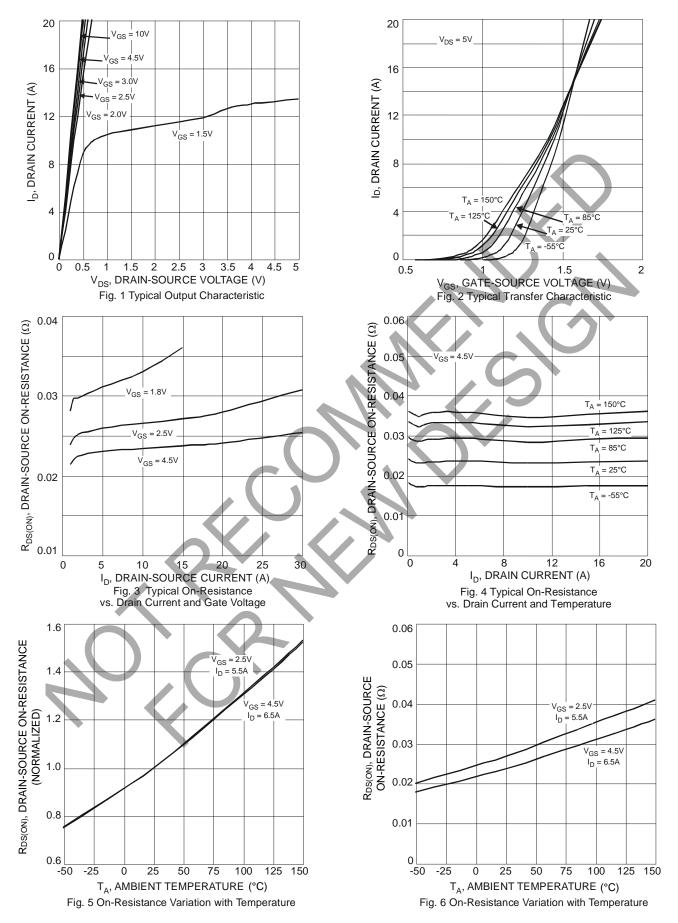
### Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

				<b>T.</b>		
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	20	_	-	V	$V_{GS} = 0V, I_{D} = 250\mu A$
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	IDSS	1	_	1.0	μA	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V
Gate-Source Leakage	Igss	_		±10	μA	$V_{GS} = \pm 10V$ , $V_{DS} = 0V$
Gate-Source Breakdown Voltage	BVsgs	±12	_		V	$V_{DS} = 0V, I_{G} = \pm 250 \mu A$
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	Vgs(TH)	0.5		0.9	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$
			21	25		V <sub>G</sub> S = 4.5V, I <sub>D</sub> = 6.5A
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	->	23	29	mΩ	$V_{GS} = 2.5V, I_D = 5.5A$
			28	36		$V_{GS} = 1.8V, I_D = 3.5A$
Forward Transfer Admittance	Y <sub>fs</sub>		8		S	V <sub>DS</sub> = 10V, I <sub>D</sub> = 5A
DYNAMIC CHARACTERISTICS (Note 7)		7				
Input Capacitance	Ciss	_	151	_	pF	
Output Capacitance	Coss	_	91	_	pF	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0V f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	32	_	pF	1 – 1.000112
Total Gate Charge	Qg	_	8.5	_	nC	
Gate-Source Charge	Qgs	_	1.6	_	nC	V <sub>G</sub> S = 4.5V, V <sub>D</sub> S = 10V, I <sub>D</sub> = 6.5A
Gate-Drain Charge	Qgd	_	2.8	_	nC	
Turn-On Delay Time	tD(ON)	_	54		ns	
Turn-On Rise Time	t <sub>R</sub>	_	66	_	ns	V <sub>DD</sub> = 10V, V <sub>GS</sub> = 4.5V,
Turn-Off Delay Time	tD(OFF)	_	613	_	ns	$R_L = 10\Omega$ , $R_G = 6\Omega$ , $I_D = 1A$
Turn-Off Fall Time	tF		205	_	ns	

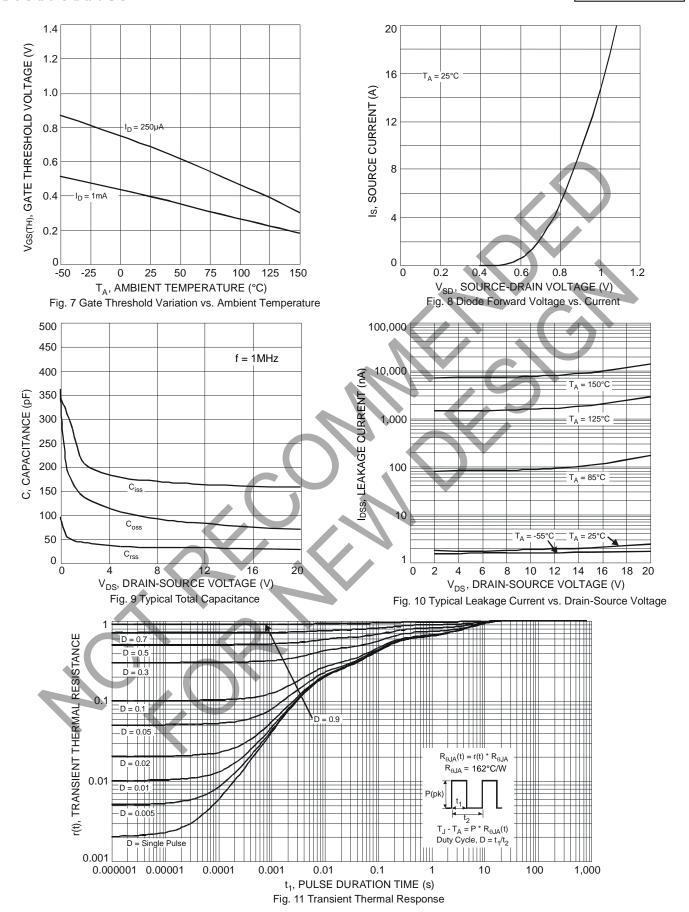
Notes:

- 5. Device mounted on FR-4 substrate PC board, 2oz. copper, with thermal vias to bottom layer 1 inch square copper plate. 6 Short duration pulse test used to minimize self-heating effect.
- 7. Guaranteed by design. Not subject to production testing.







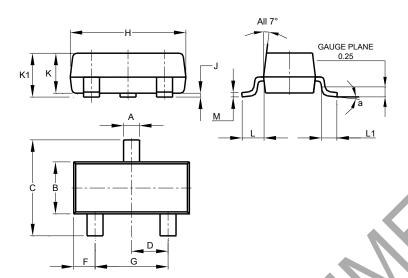




### **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT23

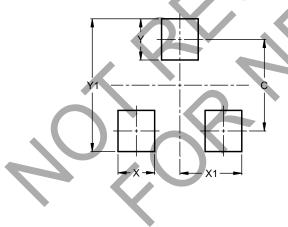


SOT23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
C	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
7	0.013	0.10	0.05			
K	0.890	1.00	0.975			
K1	0.903	1.10	1.025			
۲	0.45	0.61	0.55			
L1	0.25	0.55	0.40			
M	0.085	0.150	0.110			
а	0°	8°				
All	Dimens	ions in	mm			

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.





Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Υ	0.9
Y1	29



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